

Metal Photocathodes: The Influence of Electronic Band Structure on Transverse Emittance

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Brightness: Transverse Emittance

- Measure of transverse electron beam (or pulse) quality:

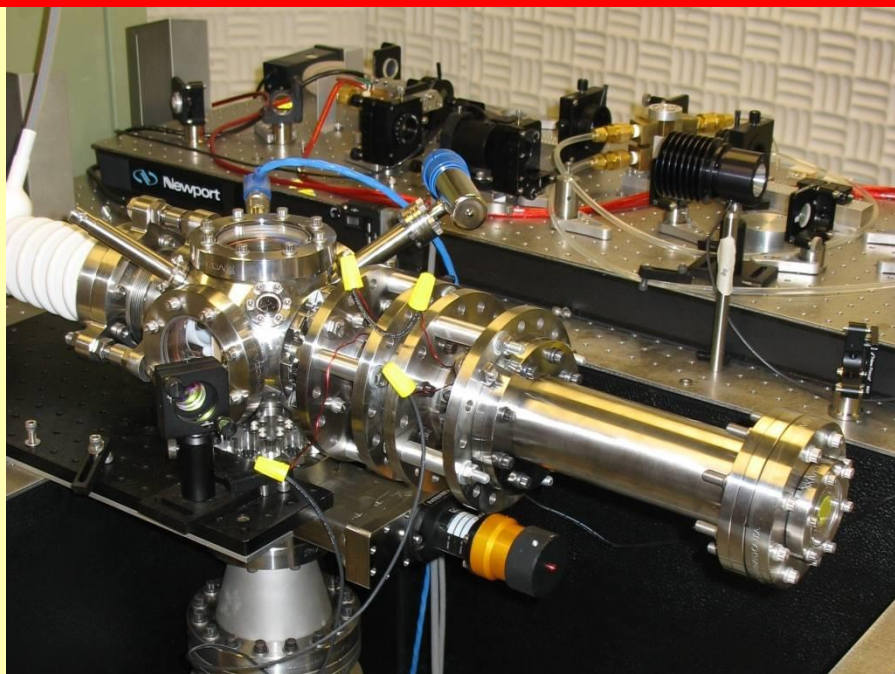
$$\varepsilon_T = \frac{\hbar}{mc} \sqrt{\langle x^2 \rangle \langle k_x^2 \rangle} = \frac{1}{mc} \Delta x \Delta p_T$$

... a conserved quantity in a ‘perfect’ system.

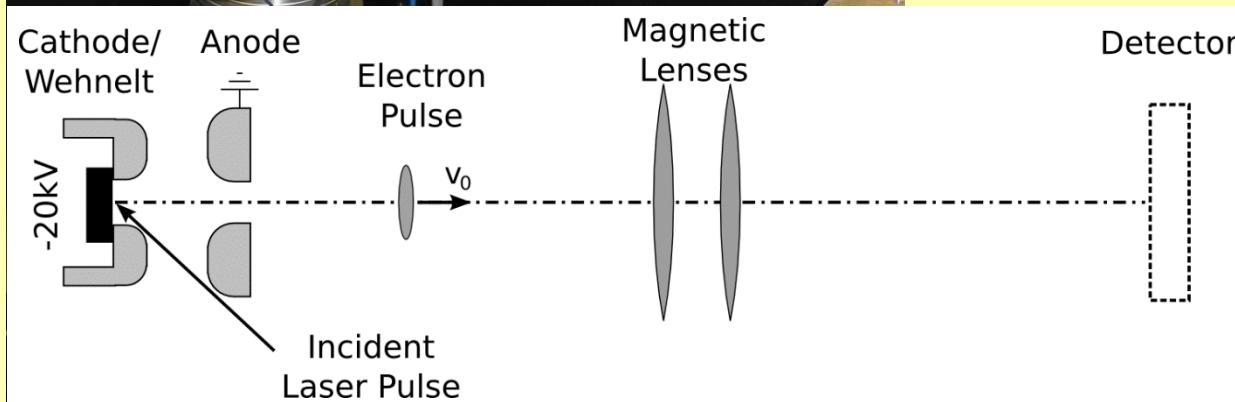
- Initial electron source parameters at photocathode:
 - Δx determined by laser spot size & limited by Child’s Law
 - Δp_T is an *intrinsic* property of the photocathode material
- *Standard* theoretical expressions for transverse rms momentum:

- Single-photon photoemission: $\Delta p_T = \sqrt{\frac{m(\hbar\omega - \phi_{eff})}{3}}$

Experiment: Solenoid Scan

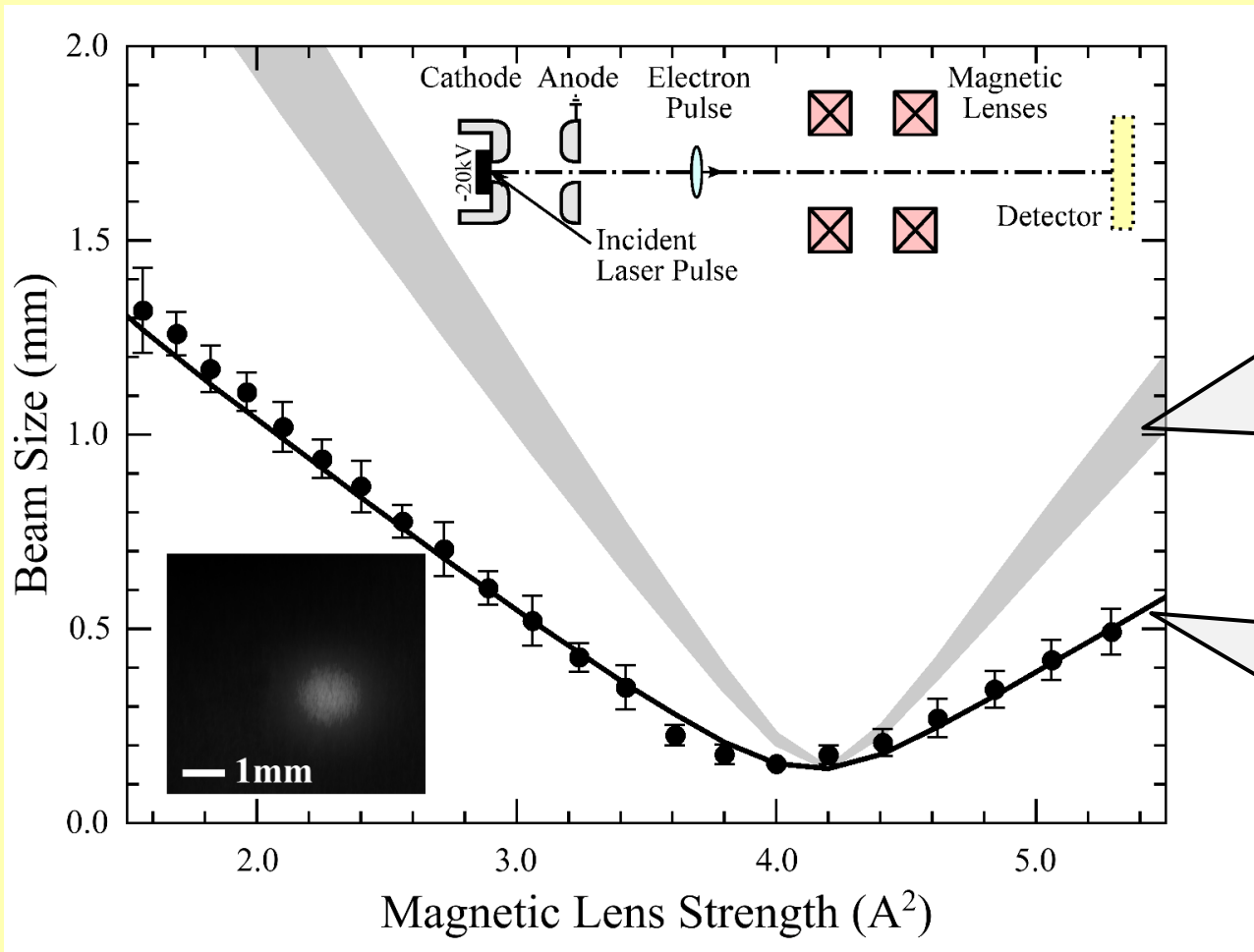


- 2W, 250fs, 63MHz, diode-pumped Yb:KGW laser
 - $\sim 4\text{ps}$ at 261nm ($\hbar\omega = 4.75\text{eV}$)
- YAG scintillator optically coupled to CCD camera
 - Beam size vs. magnetic coil (lens) current measured
 - Analytical Gaussian (AG) pulse propagation model to extract Δp_T



Results: Polycrystalline Cr

– Solenoid scan measurement



Range for Δp_T from

$$\Delta p_T = \sqrt{\frac{m_0(\hbar\omega - \phi)}{3}}$$

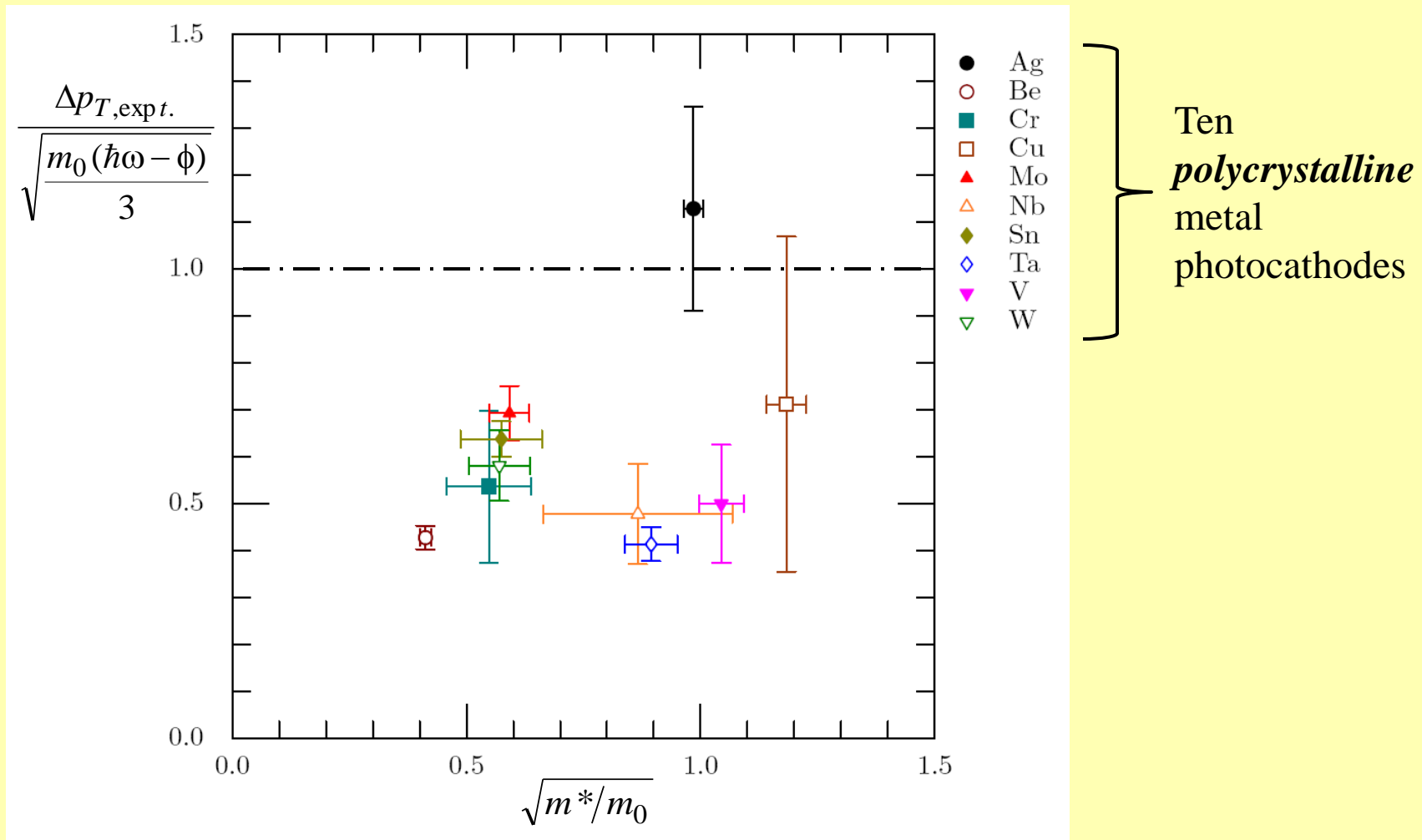
... $\phi = 4.50(\pm 0.05)\text{eV}$
and $\hbar\omega = 4.75\text{eV}$

AG model simulation
of experiment gives

$$\Delta p_T = 0.155(\pm 0.01) \\ (m_0 \cdot \text{eV})^{1/2}$$

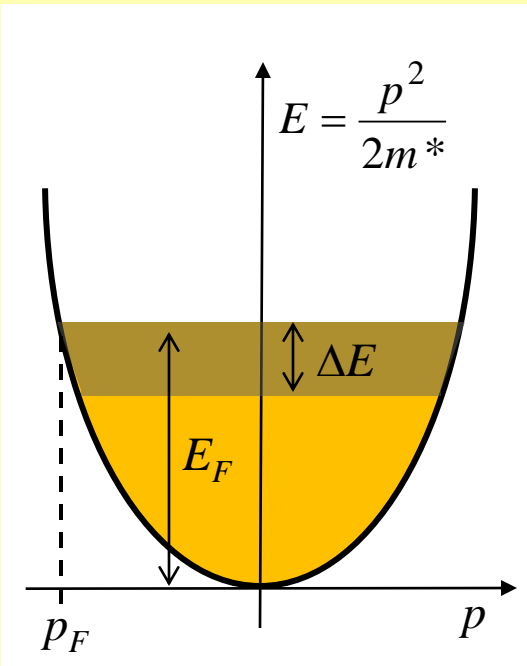
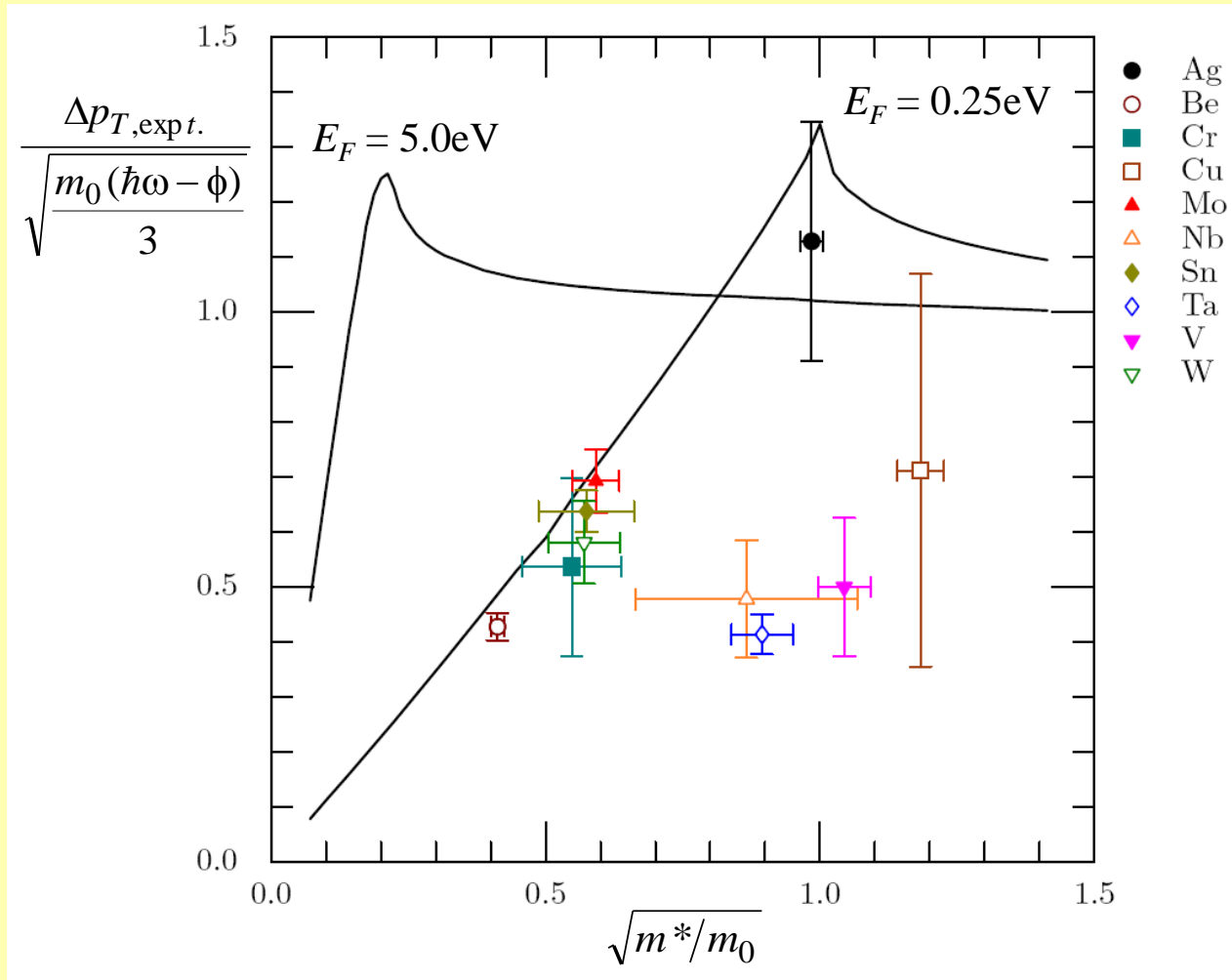
Results: Metals

– Effective mass in metal photocathodes: dH-vA, CR, $C_e = \gamma T_e$, optical, ...



Results: Metals

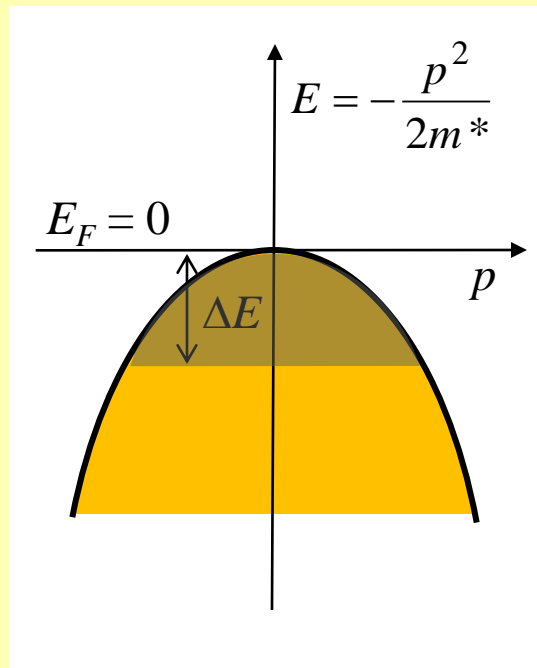
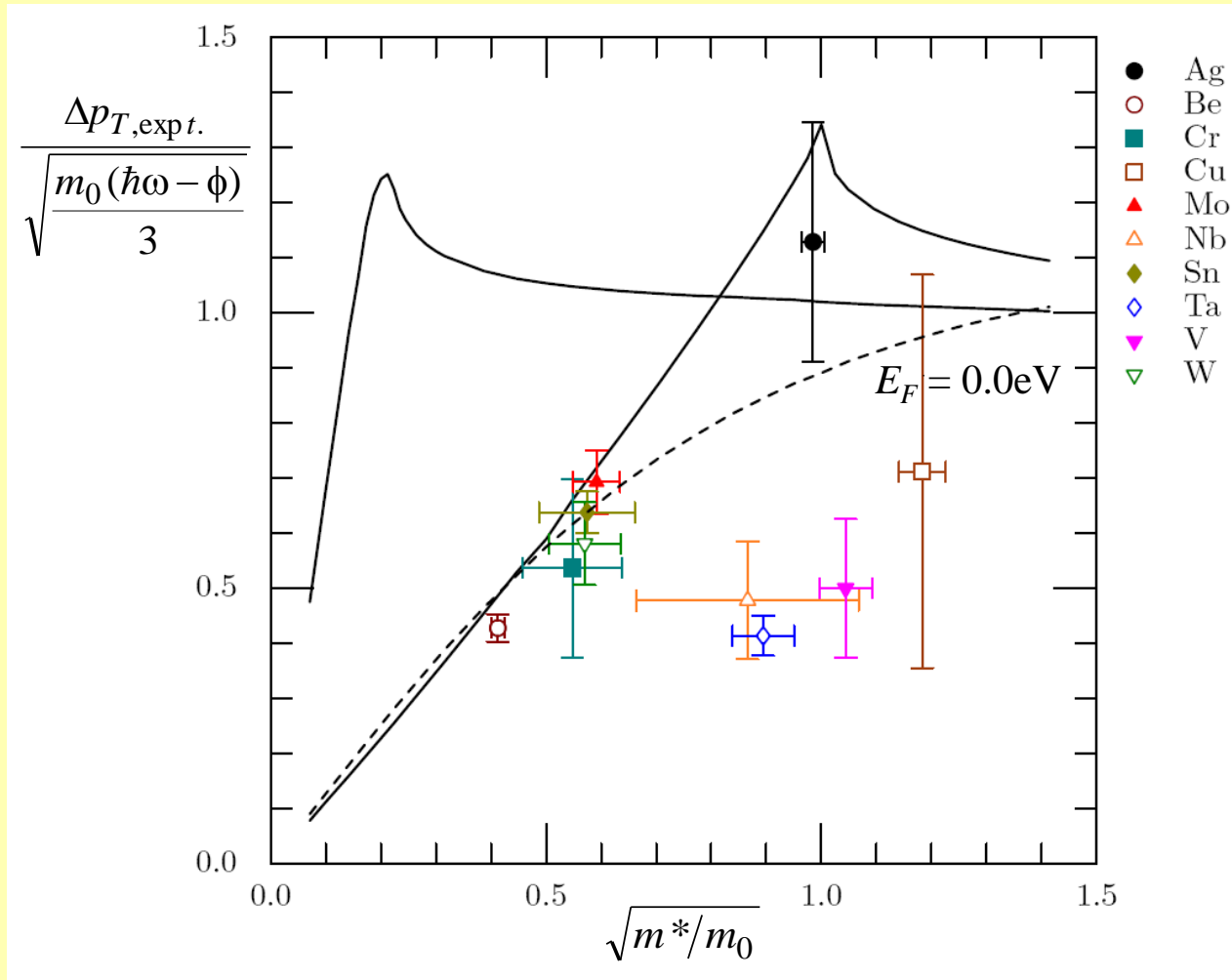
– Spherically symmetric electron-like bands: $\Delta E = \hbar\omega - \phi = 0.25\text{eV}$



Δp_T reduced when
 $p_F = \sqrt{2m^* E_F}$
 is less than
 $p_{T, \text{max.}} = \sqrt{2m_0 \Delta E}$

Results: Metals

– Hole-like bands (dashed line): $\Delta E = \hbar\omega - \phi = 0.25\text{eV}$

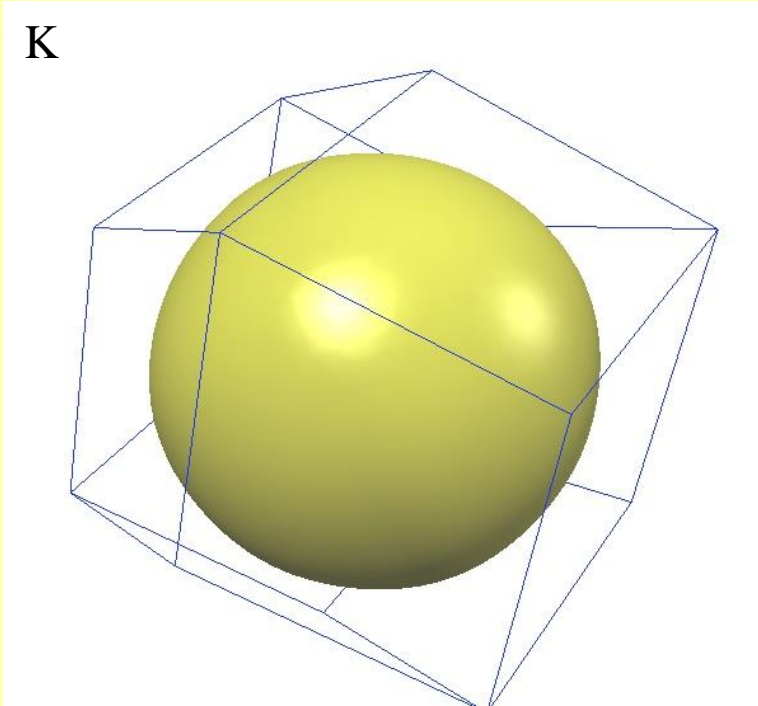


Additional effect of
low barrier
transmission $T(p_z, p_{z0})$
for high p_T states

Fermi Surfaces

UIC

K

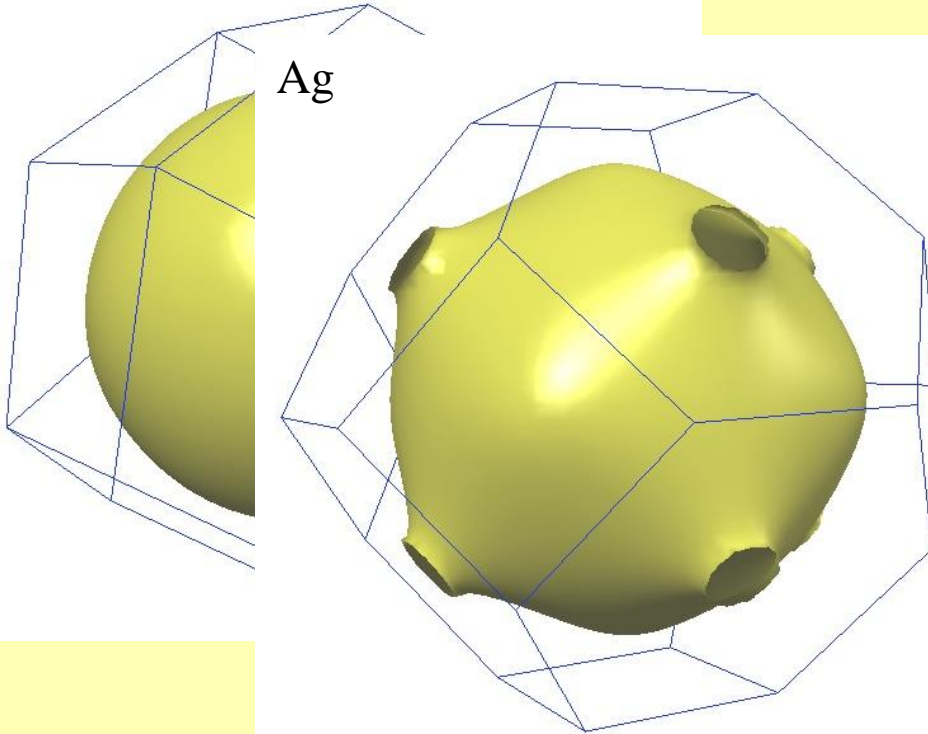


Fermi Surfaces

UIC

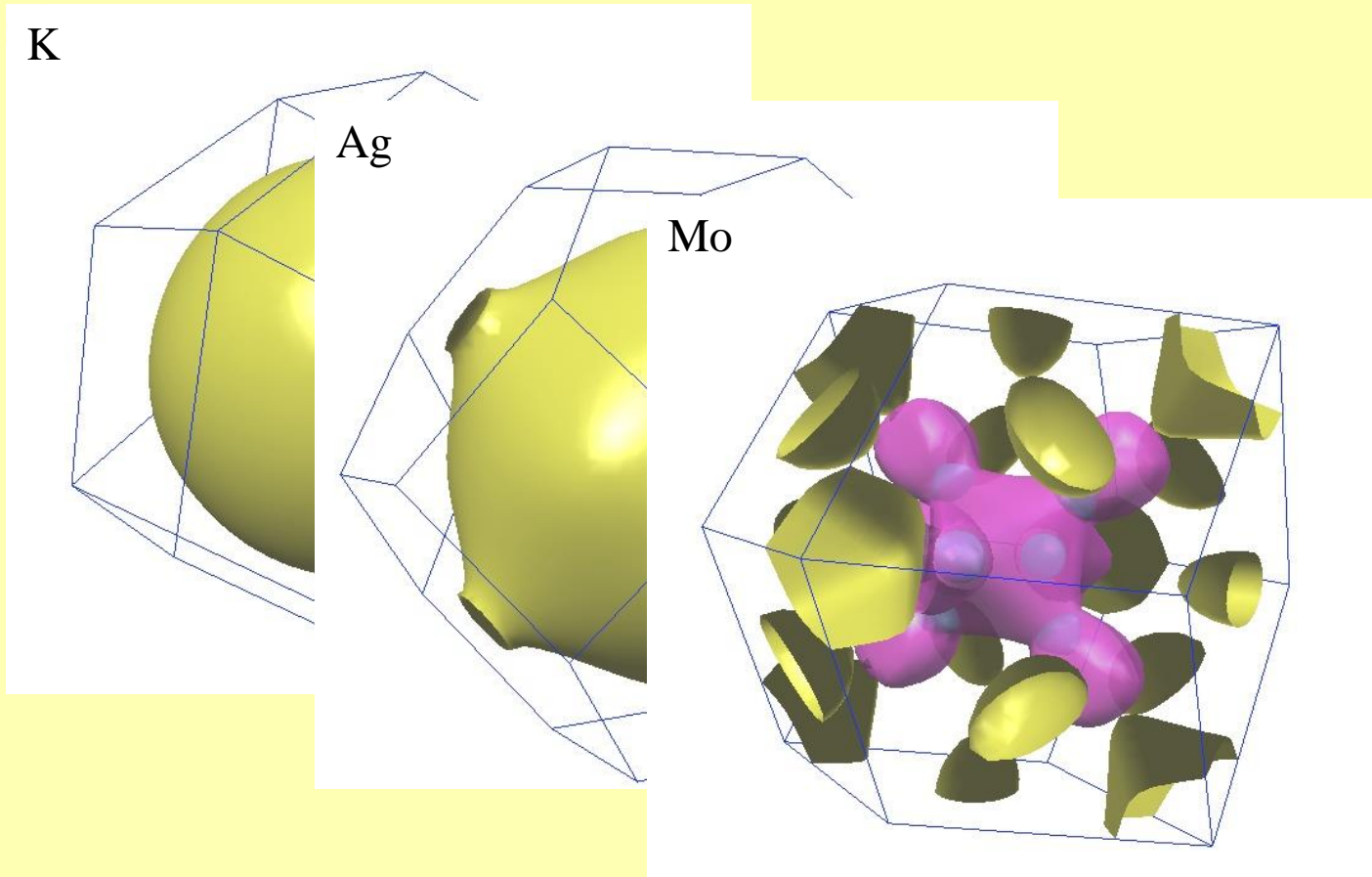
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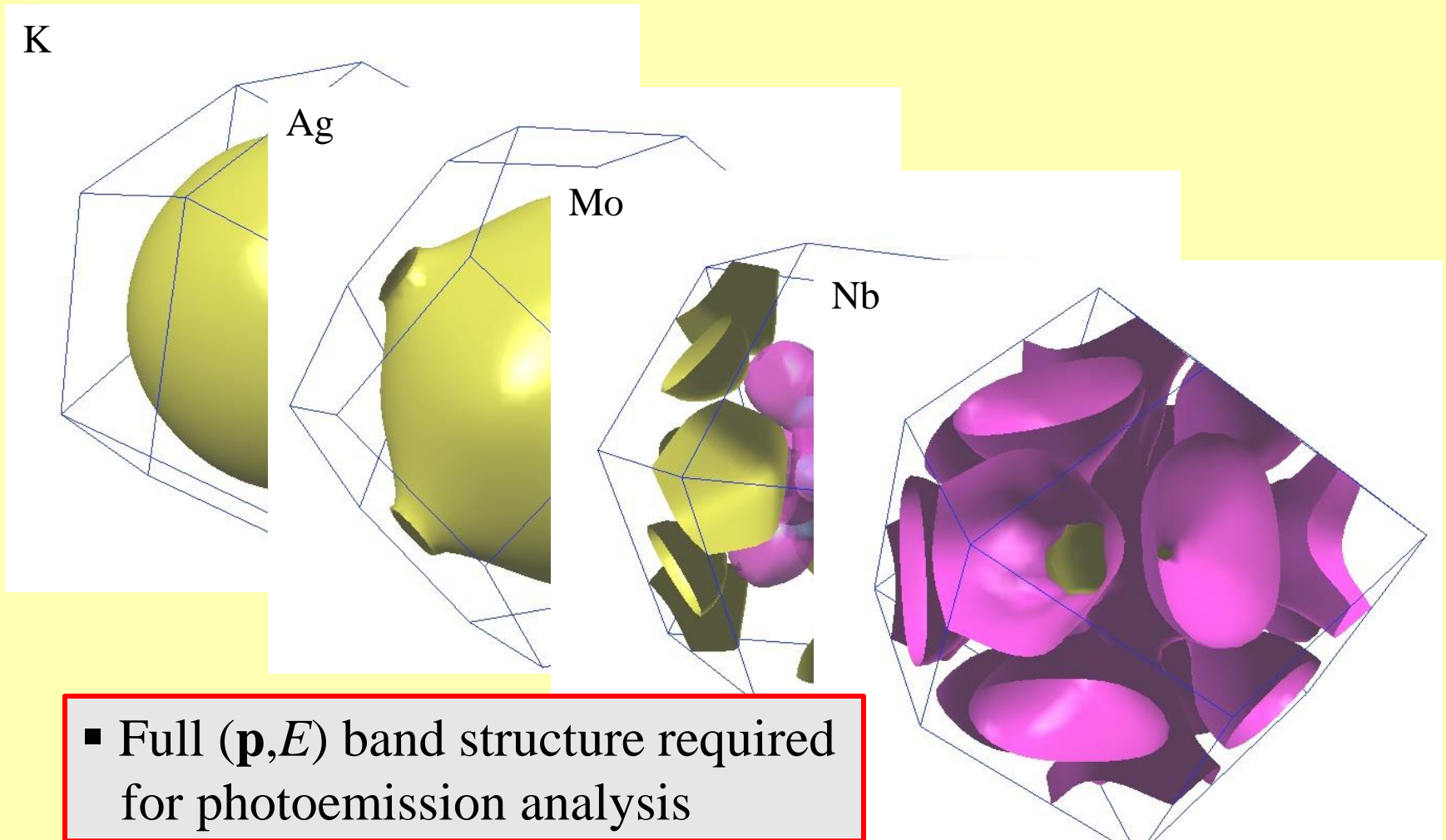
Ag



Fermi Surfaces

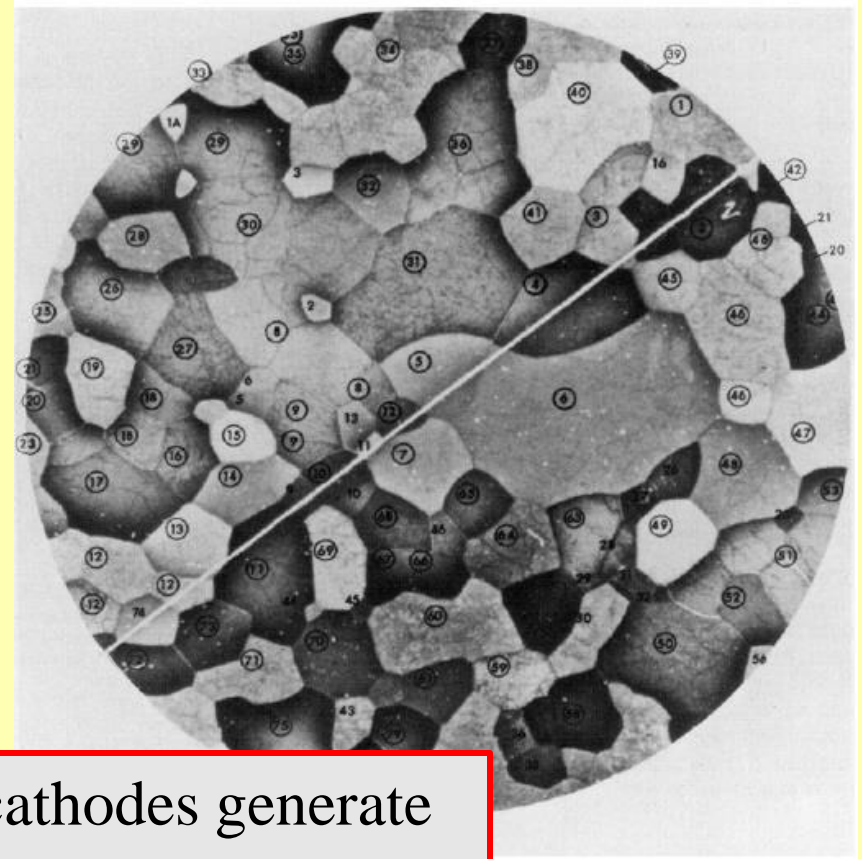
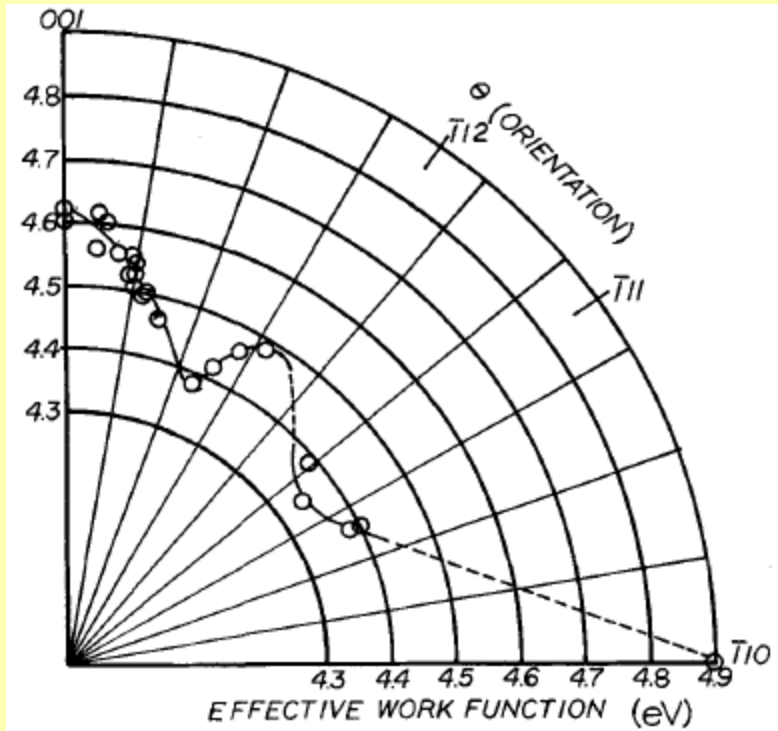
UIC





Work Function Anisotropy

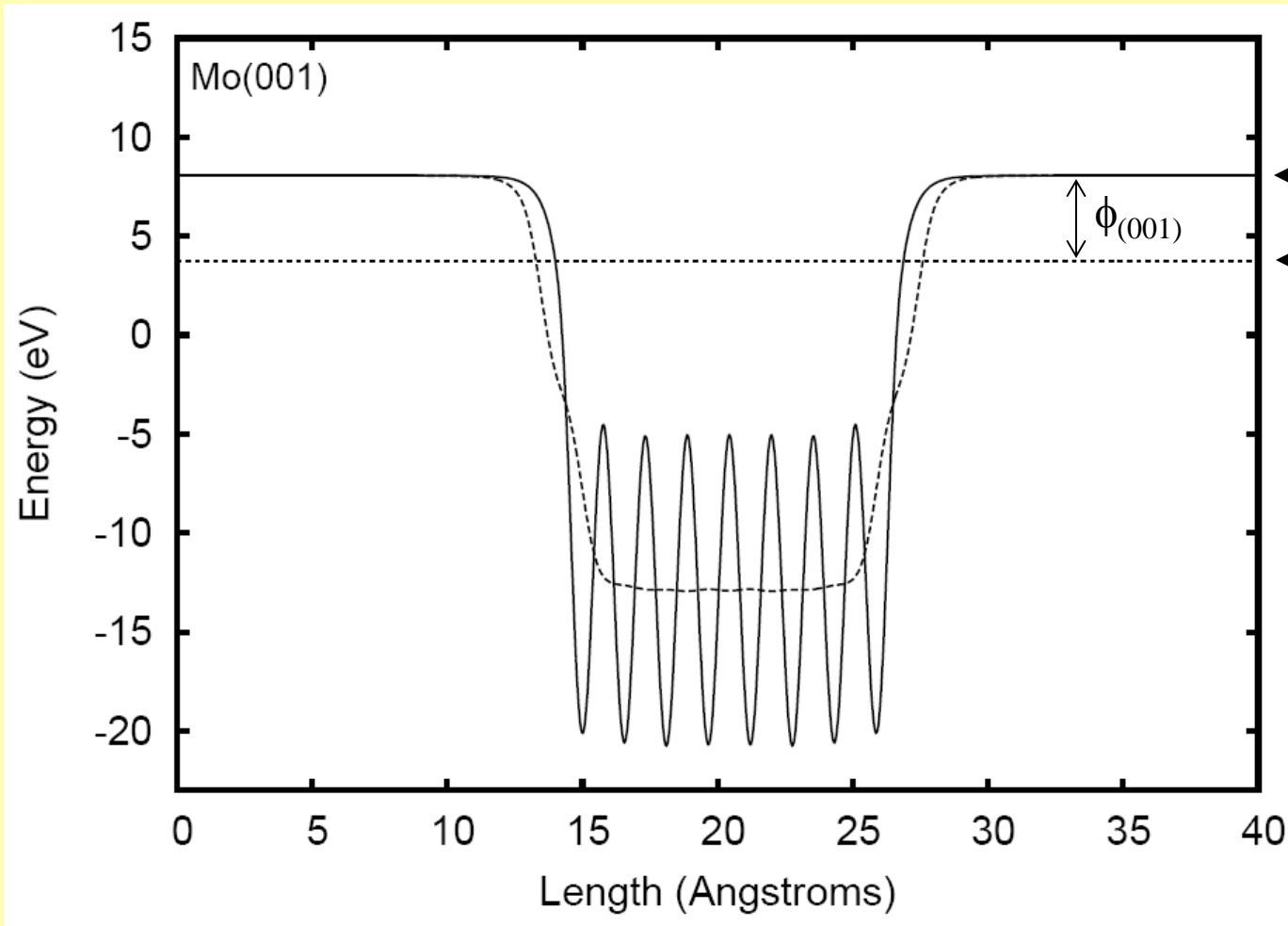
– Example: $\phi_{(ijk)}$ for Mo by electron emission microscopy



- Polycrystalline metal photocathodes generate *inhomogeneous* electron beams
- Any photoemission analysis **must** include $\phi_{(ijk)}$

Thin-slab Evaluation of $\phi_{(ijk)}$

– Example: $\phi_{(001)} = 4.53(\pm 0.05)\text{eV}$ for Mo



NOTE

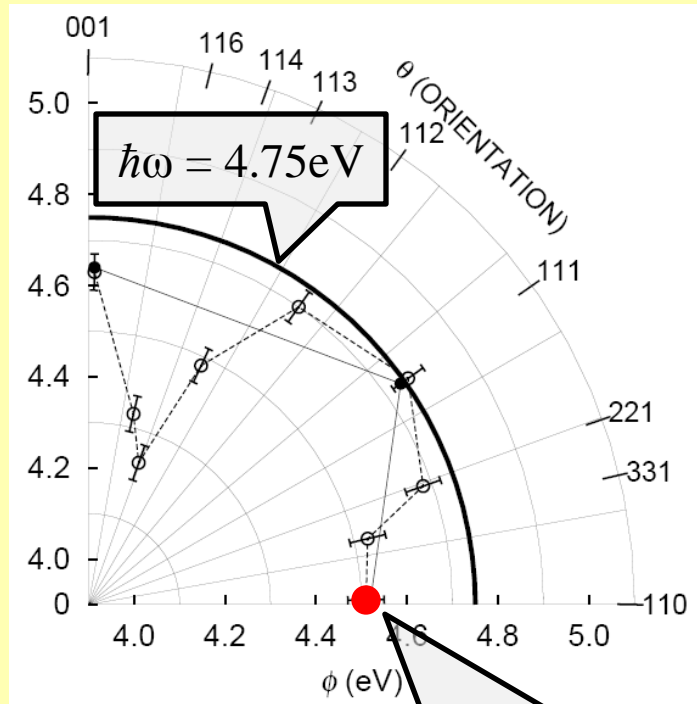
Schottky effect *not* included:

$$\frac{e}{2} \sqrt{\frac{eE_{DC}}{\pi\epsilon_0}} \approx \pm 50\text{meV}$$

uncertainty in $\phi_{(ijk)}$

Photoemission Simulation: Ag

– fcc crystal lattice



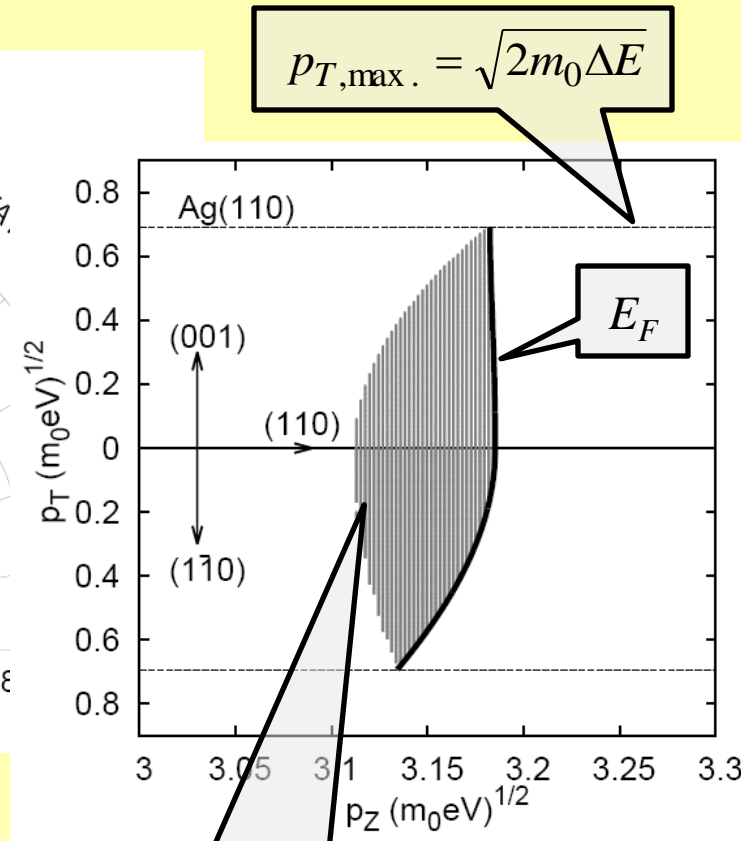
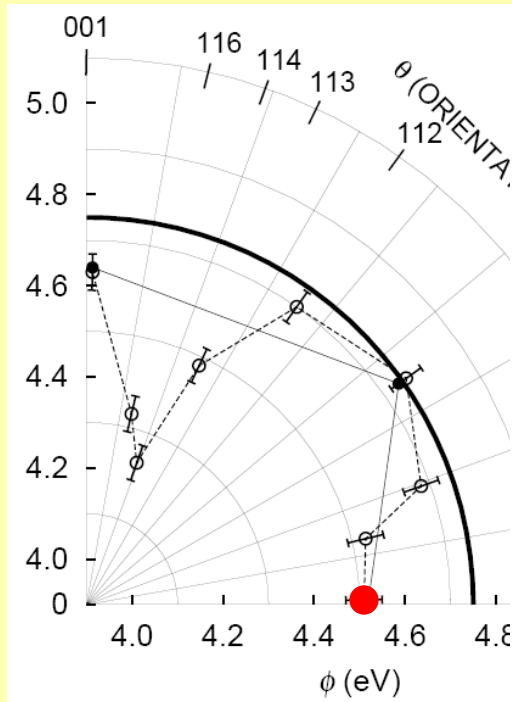
Lowest index face
with lowest $\phi_{(ijk)}$

$$\Delta E = \hbar\omega - \phi_{(110)} = 0.23\text{eV}$$

... $\pm 50\text{meV}$ error in $\phi_{(ijk)}$

Photoemission Simulation: Ag

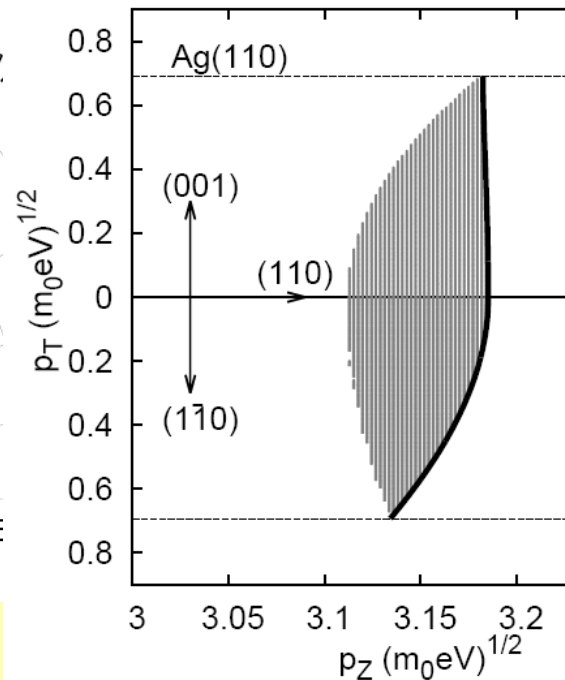
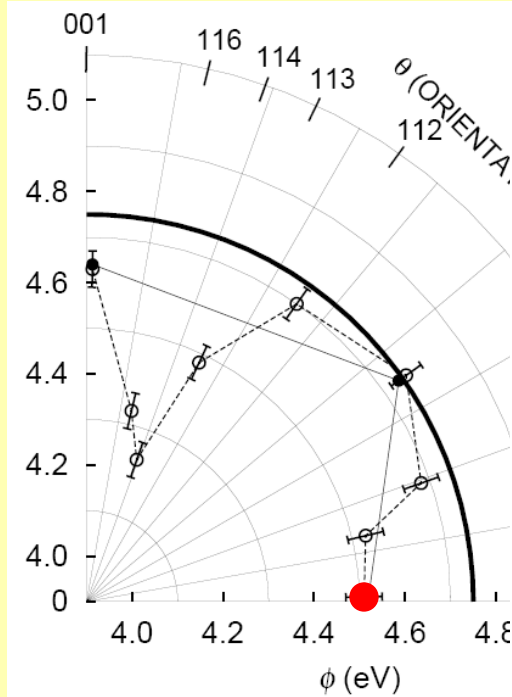
– fcc crystal lattice



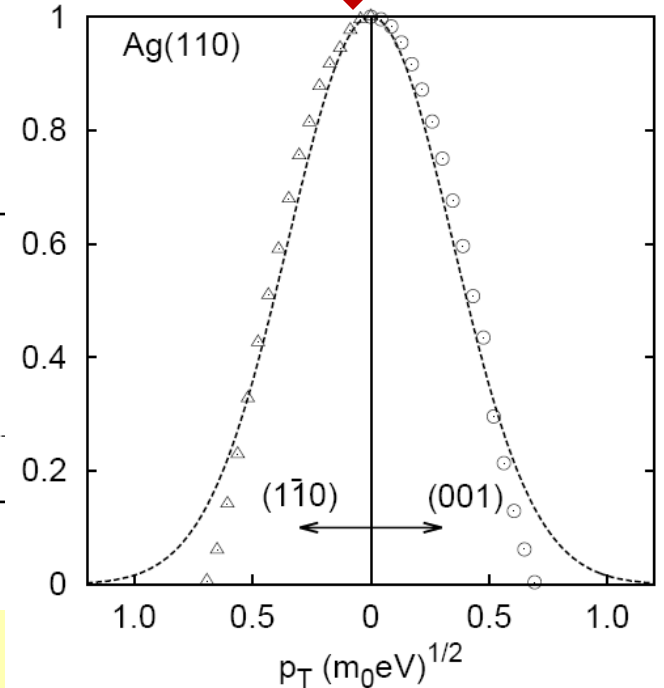
Photoemitting
electron-like states for
 $\hbar\omega = 4.75\text{eV}$
(\mathbf{p}_T and E conserved)

Photoemission Simulation: Ag

– fcc crystal lattice



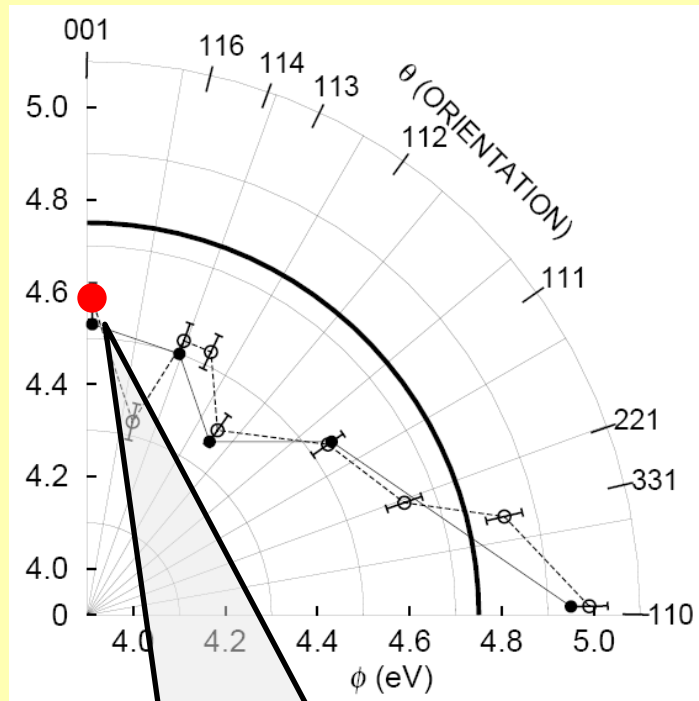
E, \mathbf{p}_T conservation
PLUS
Barrier transmission, $T(p_z, p_{z0})$



Spatially-averaged
 $\Delta p_T = 0.267 (m_0 \cdot \text{eV})^{1/2}$

Photoemission Simulation: Mo

– bcc crystal lattice



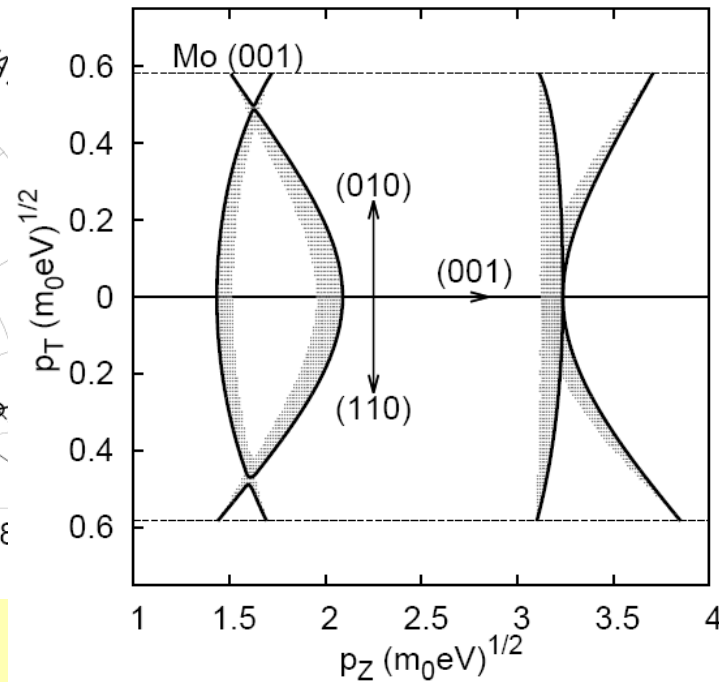
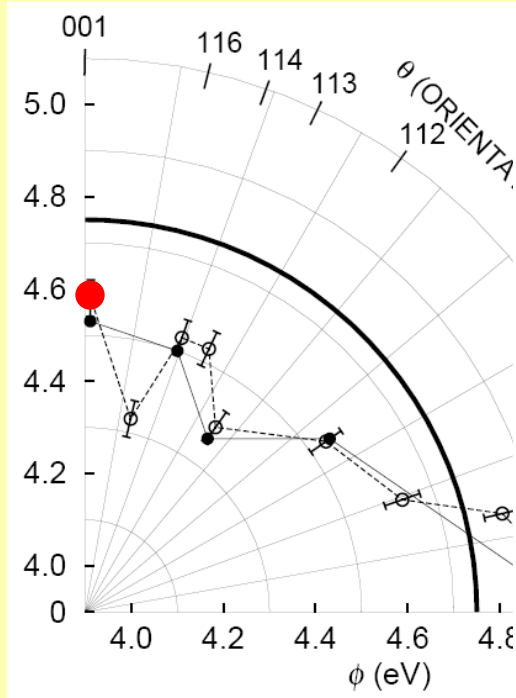
Lowest index face
with lowest $\phi_{(ijk)}$

$$\Delta E = \hbar\omega - \phi_{(001)} = 0.22\text{eV}$$

... $\pm 50\text{meV}$ error in $\phi_{(ijk)}$

Photoemission Simulation: Mo

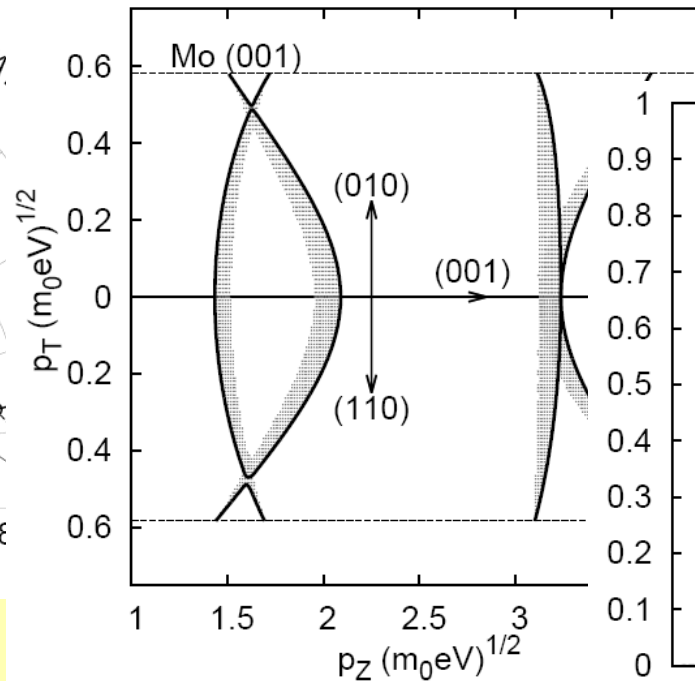
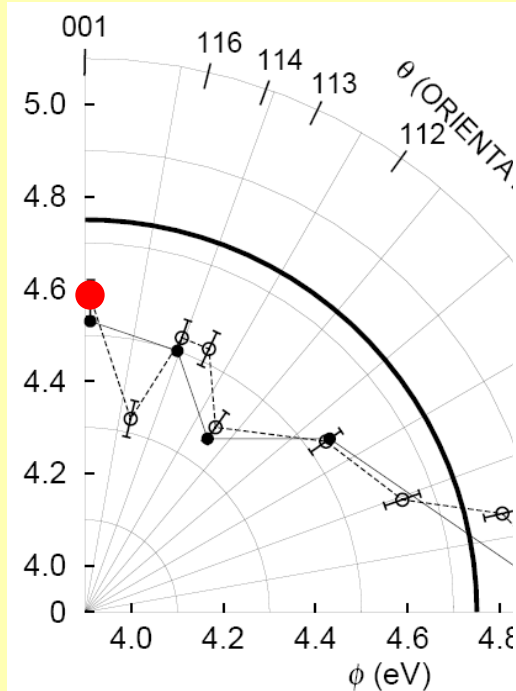
– bcc crystal lattice



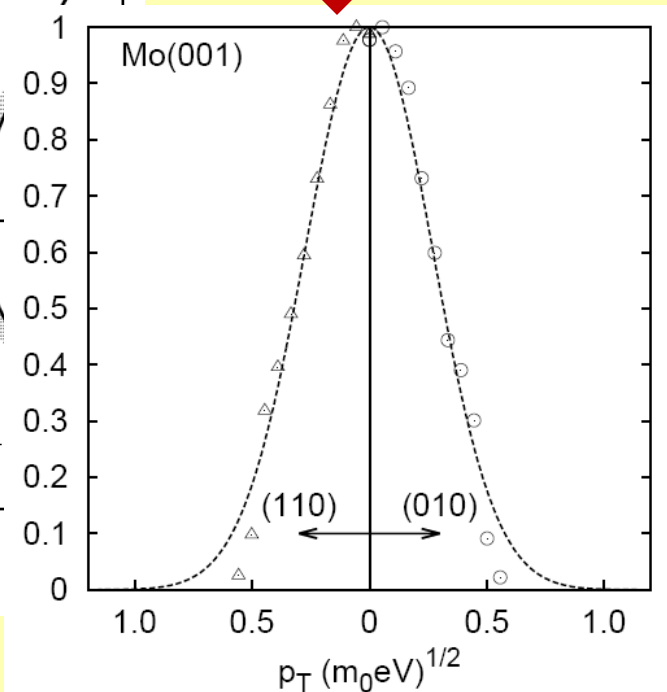
Both electron- and hole-like
states contribute to
photoemission

Photoemission Simulation: Mo

– bcc crystal lattice



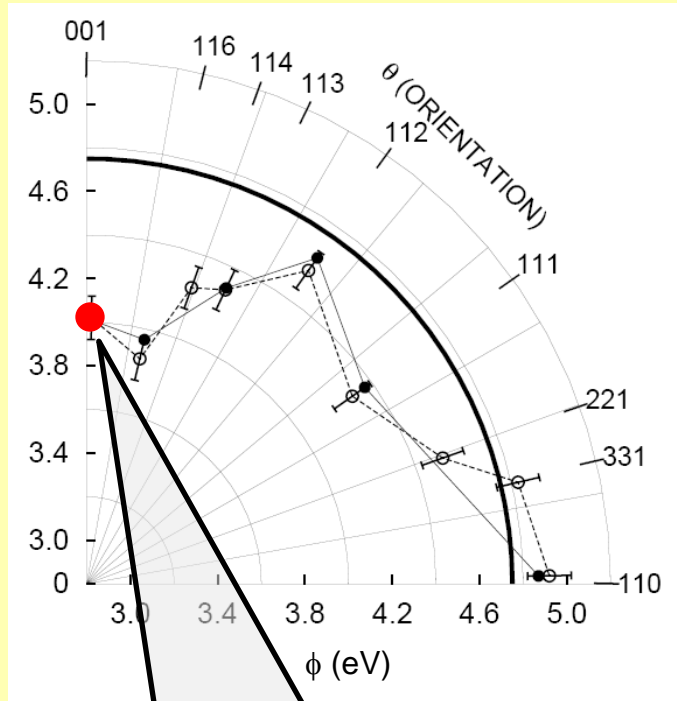
E, \mathbf{p}_T conservation
PLUS
Barrier transmission, $T(p_z, p_{z0})$



Spatially-averaged
 $\Delta p_T = 0.219$ ($m_0 \cdot eV$)^{1/2}

Photoemission Simulation: Nb

– bcc crystal lattice



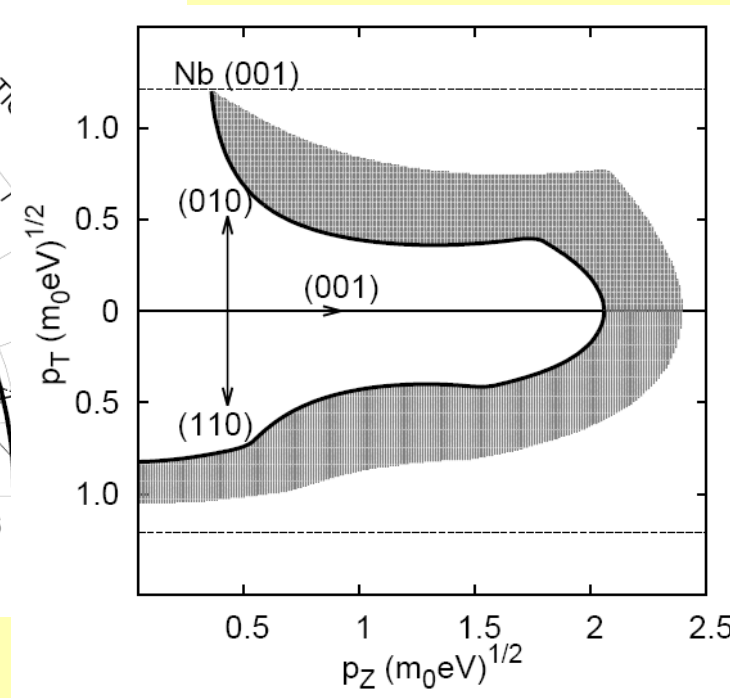
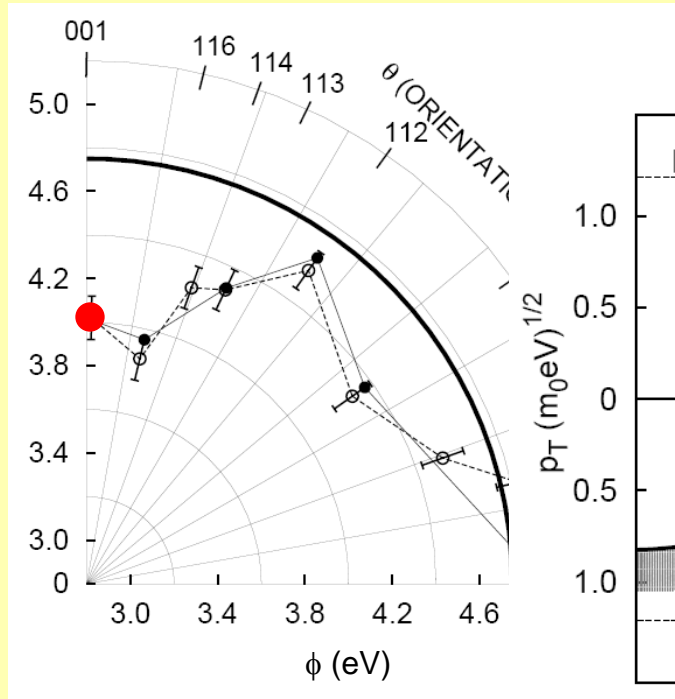
Lowest index face
with lowest $\phi_{(ijk)}$

$$\Delta E = \hbar\omega - \phi_{(001)} = 0.73\text{eV}$$

... $\pm 50\text{meV}$ error in $\phi_{(ijk)}$

Photoemission Simulation: Nb

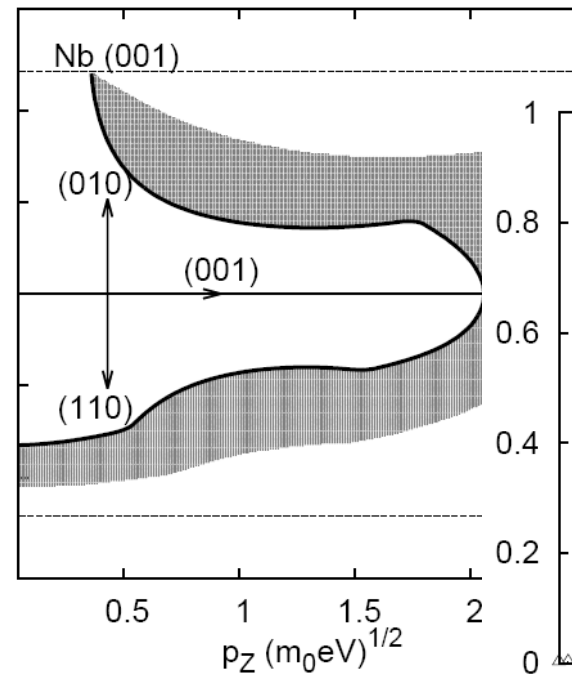
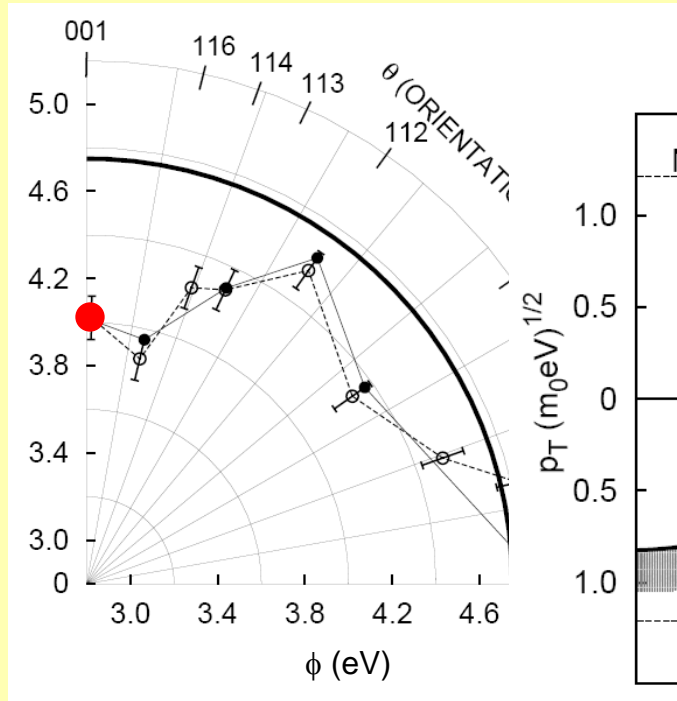
– bcc crystal lattice



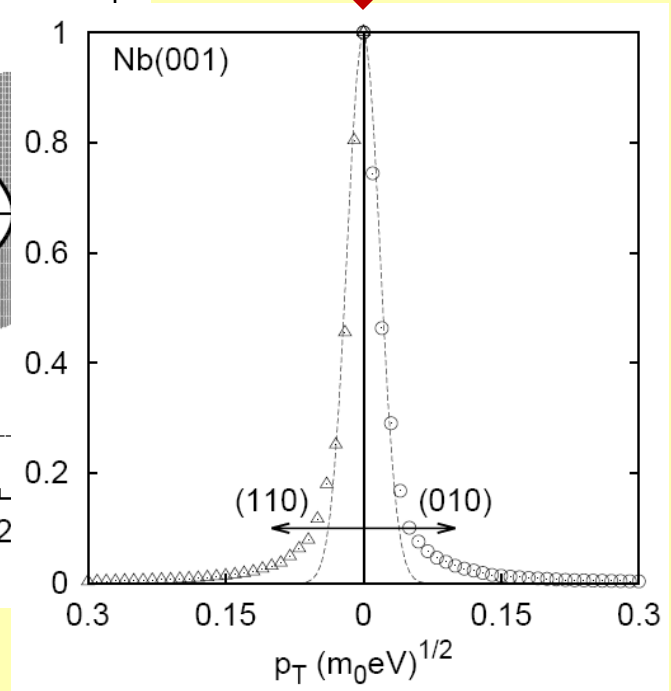
Only hole-like states contribute
to photoemission

Photoemission Simulation: Nb

– bcc crystal lattice

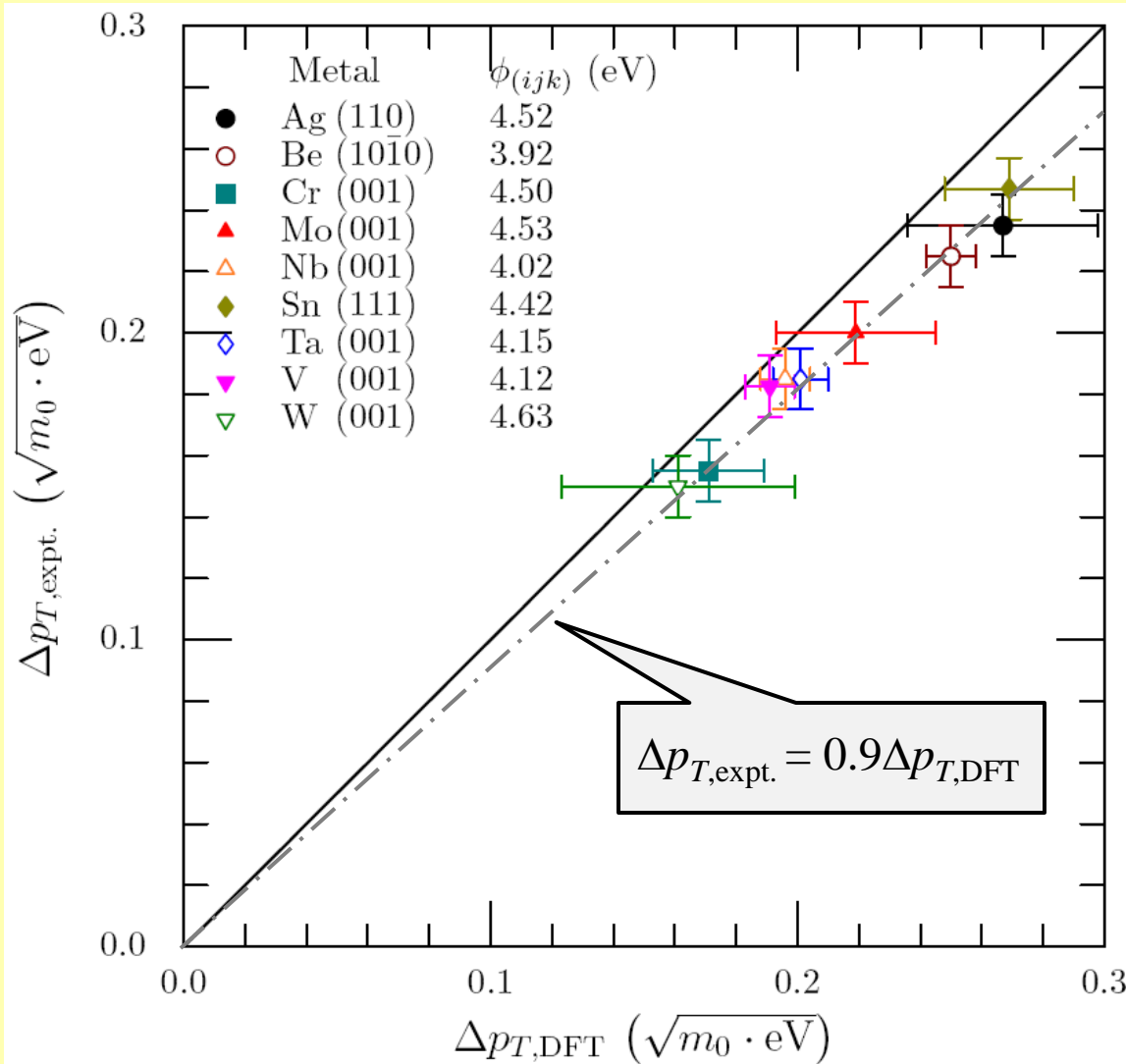


E, \mathbf{p}_T conservation
PLUS
Barrier transmission, $T(p_z, p_{z0})$



Spatially-averaged
 $\Delta p_T = 0.196 (m_0 \cdot eV)^{1/2}$

Experiment vs. Theory



NOTE

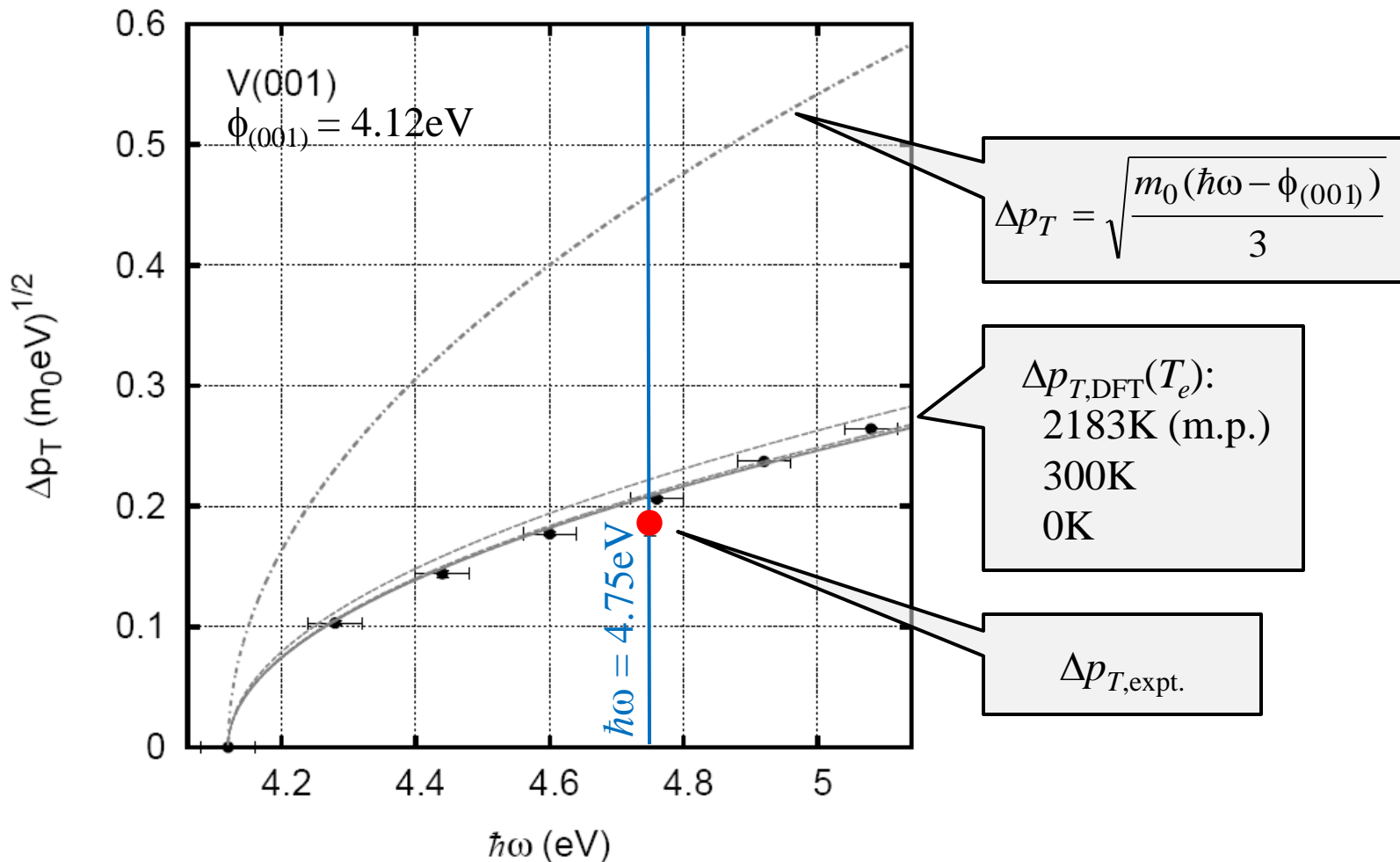
$$\Delta p_{T,\text{DFT}} \geq \Delta p_{T,\text{expt.}}$$

is *expected*:

Other crystal faces with smaller $\Delta E = \hbar\omega - \phi_{(ijk)}$ contribute with lower Δp_T thereby reducing $\Delta p_{T,\text{expt.}}$ for polycrystalline metal photocathodes.

$\Delta p_T(T_e)$ for V(001) emission

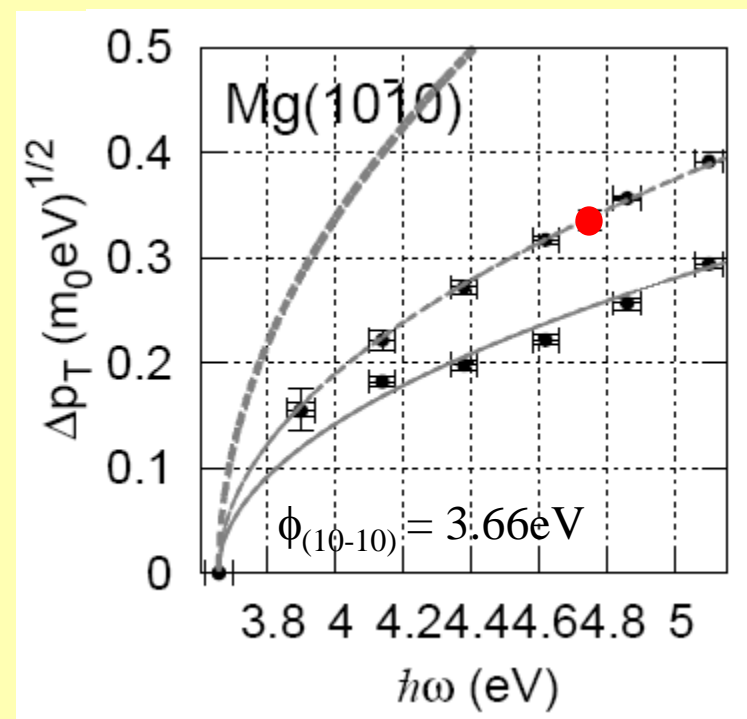
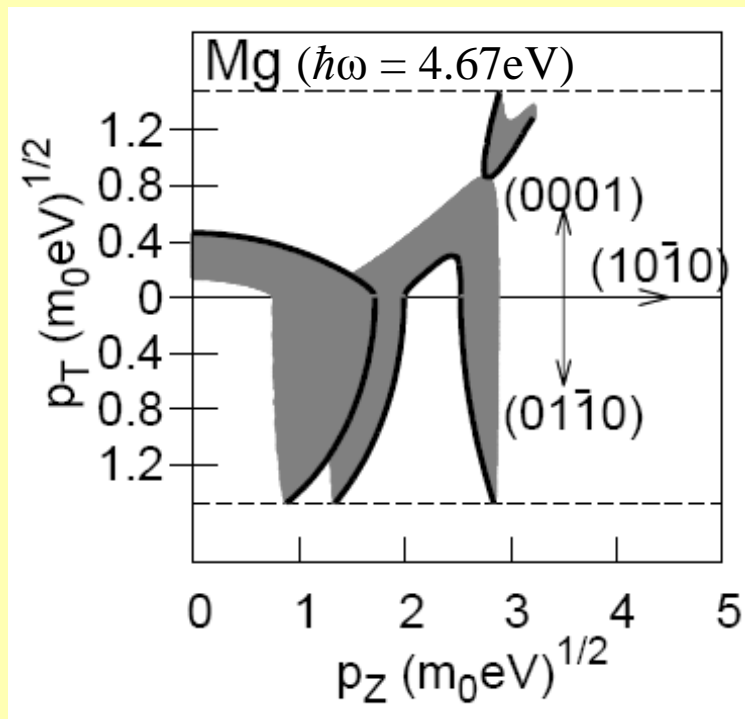
– DFT band structure with Fermi-Dirac distribution for electrons



- Work function anisotropy $\phi_{(ijk)}$
 - ⇒ Intrinsically inhomogeneous electron beam from polycrystalline photocathodes
- Band structure complexity (non-spherical Fermi surface)
 - ⇒ DFT-based photoemission analysis for evaluation of Δp_T (knowledge of electronic state (\mathbf{p}, E) -distribution is fundamental)
- Future work: Single-crystal photocathodes
 - Direct comparison with theory
 - Homogeneous electron beams (higher η_{PE} possible)
 - Bi-metal crystal alloys to ‘tune’ photocathode properties ?
 - Semiconductors ...

Calculating $\Delta p_T(ijk)$ for *all* elemental metals

- Results will be available on-line to research community in early 2015



... data presentation ?

Thank you!

Copper Photocathode

– Possible excited state emission process for Cu(111)

